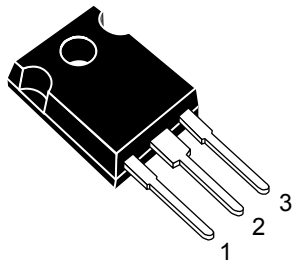
STW48N60DM2

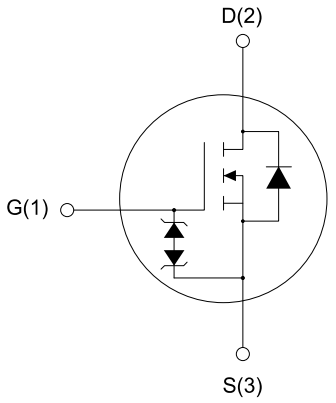
N-channel 600 V, 0.065 Ω typ., 40 A MDmesh™ DM2 Power MOSFET in a TO-247 package

Datasheet - production data



TO-247

Figure 1: Internal schematic diagram



Features

Order code	V_{DS}	$R_{DS(on)}$ max.	I_D
STW48N60DM2	600 V	0.079 Ω	40 A

- Fast-recovery body diode
- Extremely low gate charge and input capacitance
- Low on-resistance
- 100% avalanche tested
- Extremely high dv/dt ruggedness
- Zener-protected

Applications

- Switching applications

Description

This high voltage N-channel Power MOSFET is part of the MDmesh™ DM2 fast recovery diode series. It offers very low recovery charge (Q_{rr}) and time (t_{rr}) combined with low $R_{DS(on)}$, rendering it suitable for the most demanding high efficiency converters and ideal for bridge topologies and ZVS phase-shift converters.

Table 1: Device summary

Order code	Marking	Package	Packing
STW48N60DM2	48N60DM2	TO-247	Tube

1 Electrical ratings

Table 2: Absolute maximum ratings

Symbol	Parameter	Value	Unit
V_{GS}	Gate-source voltage	±25	V
I_D	Drain current (continuous) at T_{case} = 25 °C	40	A
	Drain current (continuous) at T_{case} = 100 °C	25	
I_{DM}(1)	Drain current (pulsed)	160	A
P_{TOT}	Total dissipation at T_{case} = 25 °C	300	W
dv/dt(2)	Peak diode recovery voltage slope	50	V/ns
dv/dt(3)	MOSFET dv/dt ruggedness		
T_{stg}	Storage temperature	-55 to 150	°C
T_j	Operating junction temperature		

Notes:

(1) Pulse width is limited by safe operating area.

(2) $I_{SD} \leq 40$ A, di/dt=900 A/µs; V_{DS} peak < $V_{(BR)DSS}$, V_{DD} = 400 V.

(3) $V_{DS} \leq 480$ V.

Table 3: Thermal data

Symbol	Parameter	Value	Unit
$R_{thj\text{-}case}$	Thermal resistance junction-case	0.42	°C/W
$R_{thj\text{-}amb}$	Thermal resistance junction-ambient	50	

Table 4: Avalanche characteristics

Symbol	Parameter	Value	Unit
I_{AR}	Avalanche current, repetitive or not repetitive (Pulse width limited by T_{jmax})	7	A
E_{AR}	Single pulse avalanche energy (starting T_j = 25 °C, $I_D = I_{AR}$, V_{DD} = 50 V)	950	mJ

2 Electrical characteristics

(T_{case} = 25 °C unless otherwise specified)

Table 5: Static

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage	V_{GS} = 0 V, I_D = 1 mA	600			V
I_{DSS}	Zero gate voltage drain current	V_{GS} = 0 V, V_{DS} = 600 V			1	µA
		V_{GS} = 0 V, V_{DS} = 600 V, T_{case} = 125 °C			100	
I_{GSS}	Gate-body leakage current	V_{DS} = 0 V, V_{GS} = ±25 V			±5	µA
$V_{GS(th)}$	Gate threshold voltage	V_{DS} = V_{GS}, I_D = 250 µA	3	4	5	V
$R_{DS(on)}$	Static drain-source on-resistance	V_{GS} = 10 V, I_D = 20 A		0.065	0.079	Ω

Table 6: Dynamic

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
C_{iss}	Input capacitance	V_{DS} = 100 V, f = 1 MHz, I_D = 0 A	-	3250	-	pF
C_{oss}	Output capacitance		-	142	-	
C_{rss}	Reverse transfer capacitance		-	4.5	-	
$C_{oss\ eq.}$ (1)	Equivalent output capacitance	V_{DS} = 0 to 480 V, V_{GS} = 0 V	-	258	-	pF
R_G	Intrinsic gate resistance	f = 1 MHz, I_D= 0 A	-	4	-	Ω
Q_g	Total gate charge	V_{DD} = 480 V, I_D = 40 A, V_{GS} = 10 V	-	70	-	nC
Q_{gs}	Gate-source charge		-	18	-	
Q_{gd}	Gate-drain charge		-	28	-	

Notes:

(1) $C_{oss\ eq.}$ is defined as a constant equivalent capacitance giving the same charging time as C_{oss} when V_{DS} increases from 0 to 80% V_{DSS}.

Table 7: Switching times

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on delay time	V_{DD} = 300 V, I_D = 20 A R_G = 4.7 Ω, V_{GS} = 10 V (see	-	27	-	ns
t_r	Rise time		-	27	-	
$t_{d(off)}$	Turn-off delay time		-	131	-	
t_f	Fall time		-	9.8	-	

Table 8: Source-drain diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
I_{SD} (1)	Source-drain current		-		40	A
I_{SDM} (2)	Source-drain current (pulsed)		-		160	A
V_{SD} (3)	Forward on voltage	V_{GS} = 0 V, I_{SD} = 40 A	-		1.6	V
t_{rr}	Reverse recovery time	I_{SD} = 40 A, di/dt = 100 A/µs, V_{DD} = 60 V	-	140		ns
Q_{rr}	Reverse recovery charge		-	0.7		µC
I_{RRM}	Reverse recovery current		-	10		A
t_{rr}	Reverse recovery time	I_{SD} = 40 A, di/dt = 100 A/µs, V_{DD} = 60 V, T_j = 150 °C (see	-	256		ns
Q_{rr}	Reverse recovery charge		-	2.5		µC
I_{RRM}	Reverse recovery current		-	20		A

Notes:

(1) Limited by maximum junction temperature

(2) Pulse width is limited by safe operating area.

(3) Pulse test: pulse duration = 300 µs, duty cycle 1.5%.

Table 9: Gate-source Zener diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)GSO}$	Gate-source breakdown voltage	I_{GS} = ±250 µA, I_D = 0 A	±30	-	-	V

The built-in back-to-back Zener diodes are specifically designed to enhance the ESD performance of the device. The Zener voltage facilitates efficient and cost-effective device integrity protection,thus eliminating the need for additional external componentry.

2.2 Electrical characteristics (curves)

Figure 2: Safe operating area

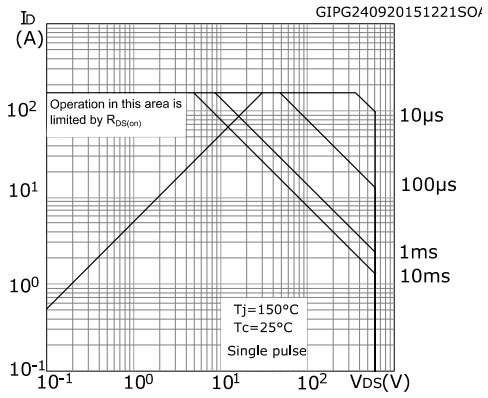


Figure 3: Thermal impedance

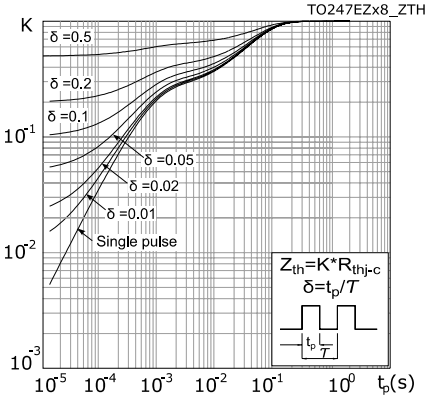


Figure 4: Output characteristics

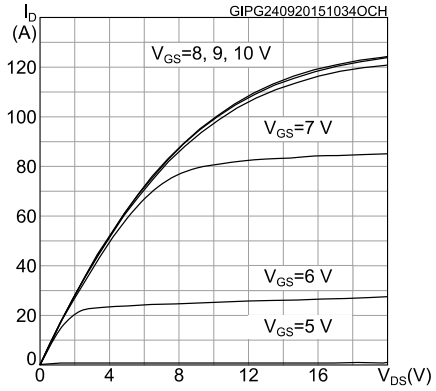


Figure 5: Transfer characteristics

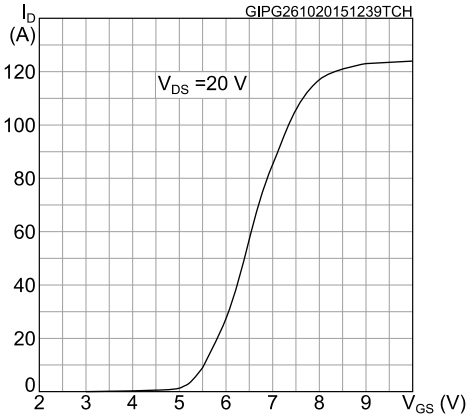


Figure 6: Gate charge vs gate-source voltage

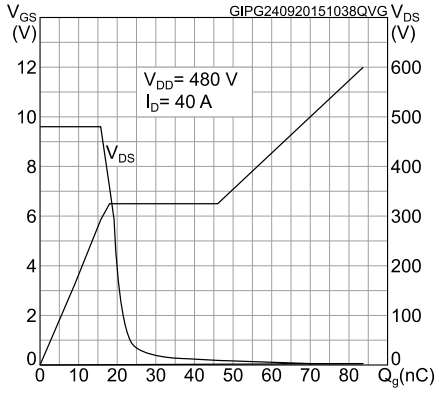


Figure 7: Static drain-source on-resistance